

REMARKS/ARGUMENTS

Claims 6-15 are new.

Support for each new and amended claim is found at the originally filed claims and throughout the originally filed specification. Additionally, support for the feature of present Claim 1 “wherein from 20 to 100 mol%” is found, for example, at page 8, line 4, of the originally filed specification. Support for the following anhydride features of present Claim 1 “1,2,3,4-cyclobutanetetracarboxylic dianhydride, 2,3,5-tricarboxycyclopentylacetic dianhydride, 3,4-dicarboxy-1,2,3,4-tetrahydro-1-naphthalenesuccinic dianhydride, bicyclo [3,3,0]octane-2,4,6,8-tetracarboxylic dianhydride and 1,2,3,4-butanetetracarboxylic dianhydride;” is found, for example at page 6, second paragraph, of the originally filed specification. Support for the feature of present Claim 1 “from 10 to 100 mol% of the diamine component” is found, for example, at page 13, first paragraph, of the originally filed specification. Support for new Claims 6-7 is found, for example, at originally filed Claim 4. Support for new Claims 8-10 is found, for example, at originally filed Claim 5. Support for new Claims 11-13 is found, for example, at originally filed Claim 1. Support for new Claims 14-15 is found, for example, at originally filed Claim 2.

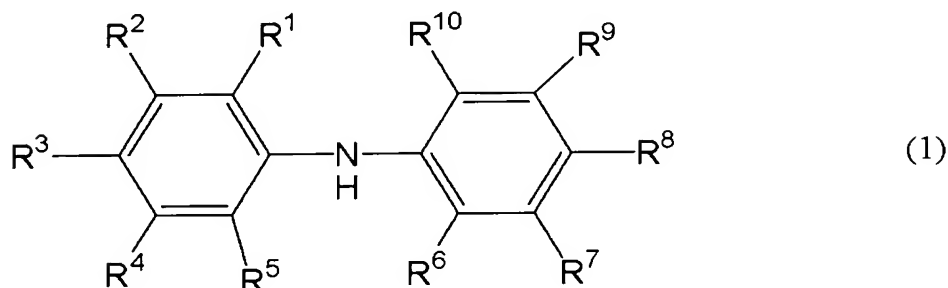
No new matter is believed to have been added.

The objection to Claims 4 and 5 is believed to be obviated by amendment of these claims.

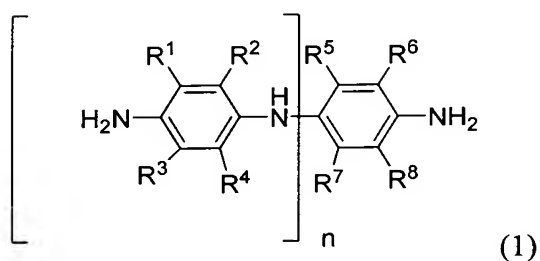
The indefiniteness rejection of Claims 1-3 is believed to be obviated by the amendment of Claim 1.

The anticipation and obviousness rejections of Claims 1-3 as being unpatentable in view of JP 2000-44683 (‘683) are respectfully traversed. ‘683 describes a diamine having for producing a coating film having a high heat resistance and a low resistance (e.g., a high conductivity) (see the Abstract of ‘683).

Applicants note that the diamines of '683 and present Claim 1 are different. As shown in present Claim 1, the diamine (1) has the structure:



In contrast, the diamine of '683 has the structure:



wherein n is an integer of 3-1000 (see paragraph 13 of '683). Accordingly, on this basis alone, '683 does not describe or suggest every feature of present Claim 1, and the claims depending therefrom, and withdrawal of the obviousness and anticipation rejections is respectfully requested.

Further, as described in present Claim 1, the tetracarboxylic dianhydride is selected from the group consisting of

- 1,2,3,4-cyclobutanetetracarboxylic dianhydride,
- 2,3,5-tricarboxycyclopentylacetic dianhydride,
- 3,4-dicarboxy-1,2,3,4-tetrahydro-1-naphthalenesuccinic dianhydride,

bicyclo [3,3,0]octane-2,4,6,8-tetracarboxylic dianhydride and  
1,2,3,4-butanetetracarboxylic dianhydride;

and is present in an amount of from 20 to 100 mol%. These features of present Claim 1, when used to produce a liquid crystal alignment film, result in the produced liquid crystal alignment film exhibiting a high voltage retention, even in a high temperature environment, which has a remarkably low accumulation charge (see page 3, lines 15-24, of the originally filed specification). The superior result of a high voltage retention, even in a high temperature environment, is not described or suggested by '683, making this superior result an unexpected result when compared to the disclosure of '683. Withdrawal of the obviousness rejection is requested on this basis alone.

Further, the superior result of having a substantially low accumulation of charge resulting from the forming films using the inventive embodiment of present Claim 1 (see page 5, lines 15-24, of the originally filed specification) is not only not described or suggested by '683, the result is actually "taught away from" by '683.

In examples 4, 5 and 6 of '683 (see paragraphs 55, line 13, paragraph 57, line 13, and paragraph 59, line 13 of '683), specific volume resistance values of polyimide films obtained in each case for films containing diamine of '683 (structure shown above) for consecutive values of n are summarized in the following Table:

	Ex. 4	Ex. 5	Ex. 6
Value of n	2	3	4
Specific volume Resistance ( $\Omega$ cm)	At a level of $10^{13}$	At a level of $10^{12}$	At a level of $10^{10}$

As shown in the Table, as n increases, specific volume resistance decreases, conductance becomes high, and accumulation of charge decreases. Thus, as shown by the data in the

Table, as n decreases by 1, specific volume increases such that one digit changes, conductance becomes low, and accumulated charge increases.

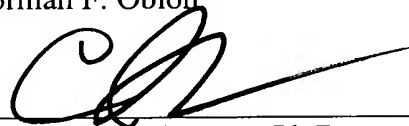
Accordingly, by further decreasing n, based on the data described above for '683, accumulated charge would be expected to increase. In contrast, a substantially low accumulation of charge results from employing the presently claimed inventive embodiment of, for example, present Claim 1 in a film. This result is not described or suggested by '683, and in fact, is "taught away from" by '683.

In light of the above presented arguments, withdrawal of the anticipation and obvious rejections is respectfully requested.

Applicants submit the present application is now in condition for allowance. Early notification to this effect is earnestly solicited.

Respectfully submitted,

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